

SN74AHC595 具有三态输出寄存器的 8 位移位寄存器

1 特性

- 工作范围：2V 至 5.5V V_{CC}
- 8 位串行输入、并行输出移位寄存器
- 门锁性能超过 100mA，符合 JESD 78 II 类规范
- ESD 保护性能超过 JESD 22 规范要求
 - 2000V 人体放电模型 (A114-A)
 - 1000V 充电器件模型 (C101)

2 应用

- 网络交换机
- 电力基础设施
- LED 显示屏
- 服务器

3 说明

SN74AHC595 器件包含一个可对 8 位 D 类存储寄存器进行馈送的 8 位串行输入、并行输出移位寄存器。存储寄存器具有并行三态输出。移位寄存器和存储寄存器各自具备独立时钟。移位寄存器具有直接覆盖清除 (SRCLR) 输入以及用于级联结构的串行 (SER) 输入和串行输出。当输出使能端 ($\overline{OE}$) 输入为高电平时，所有输出 (QH' 除外) 均处于高阻抗状态。

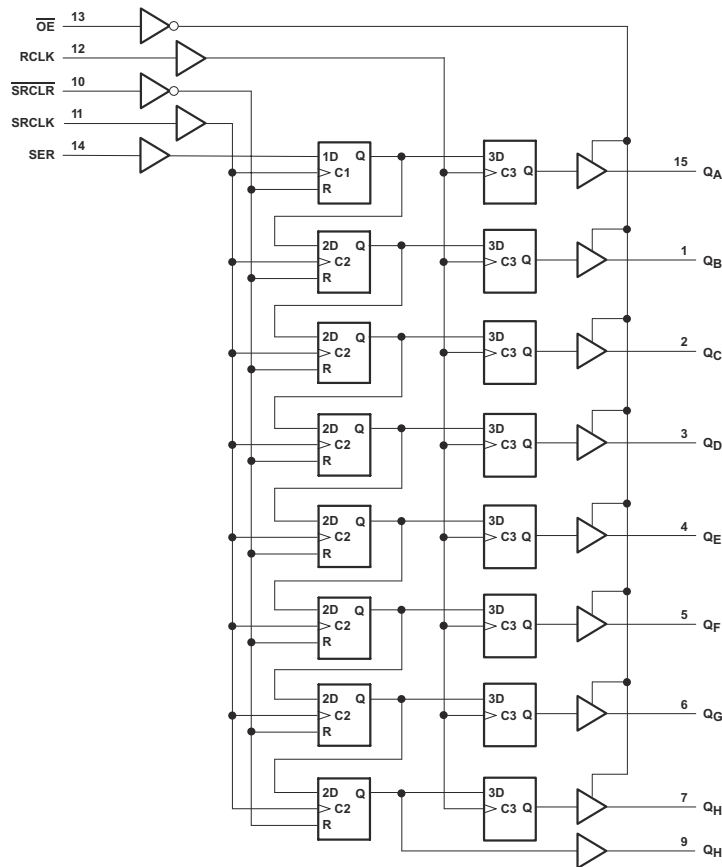
封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 ⁽²⁾	本体尺寸 ⁽³⁾
SN74AHC595	BQB (WQFN , 16)	3.5mm x 2.5mm	3.5mm x 2.5mm
	N (PDIP , 16)	19.31mm x 9.4mm	19.31mm x 6.35mm
	D (SOIC , 16)	9.90mm x 6mm	9.90mm x 3.90mm
	DB (SSOP , 16)	6.20mm x 7.8mm	6.20mm x 5.30mm
	PW (TSSOP , 16)	5.00mm x 6.4mm	5.00mm x 4.40mm

(1) 如需了解更多信息，请参阅第 11 节。

(2) 封装尺寸 (长 × 宽) 为标称值，并包括引脚 (如适用)。

(3) 本体尺寸 (长 × 宽) 为标称值，不包括引脚。



逻辑图 (正逻辑)



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4 Pin Configuration and Functions

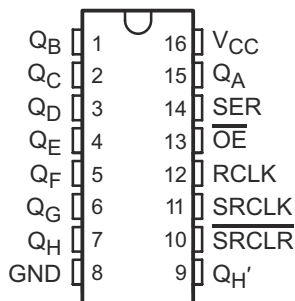


图 4-1. D, DB, N, PW Packages 16-Pin SOIC, SSOP, PDIP, TSSOP (Top View)

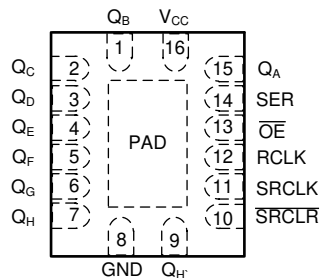


图 4-2. BQB Package, 16-Pin WQFN (Top View)

表 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
GND	8	—	Ground Pin
$\overline{OE}$	13	I	Output Enable
Q_A	15	O	Q_A Output
Q_B	1	O	Q_B Output
Q_C	2	O	Q_C Output
Q_D	3	O	Q_D Output
Q_E	4	O	Q_E Output
Q_F	5	O	Q_F Output
Q_G	6	O	Q_G Output
Q_H	7	O	Q_H Output
$Q_{H'}$	9	O	$Q_{H'}$ Output
RCLK	12	I	RCLK Input
SER	14	I	SER Input
SRCLK	11	I	SRCLK Input
SRCLR	10	I	SRCLR Input
V_{CC}	16	—	Power Pin

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	−0.5	7	V
V _I	Input voltage ⁽²⁾	−0.5	7	V
V _O	Output voltage ⁽²⁾	−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	(V _I < 0)	−20	mA
I _{OK}	Output clamp current	(V _O < 0 or V _O > V _{CC})	±20	mA
I _O	Continuous output current	(V _O = 0 to V _{CC})	±25	mA
	Continuous current through V _{CC} or GND		±75	mA
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	−65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2		5.5	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5		V
		V _{CC} = 3 V	2.1		
		V _{CC} = 5.5 V	3.85		
V _{IL}	Low-level Input voltage	V _{CC} = 2 V		0.5	V
		V _{CC} = 3 V		0.9	
		V _{CC} = 5.5 V		1.65	
V _I	Input voltage	0		5.5	V
V _O	Output voltage	0		V _{CC}	V
I _{OH}	High-level output current	V _{CC} = 2 V		−50	μA
		V _{CC} = 3.3 V ± 0.3 V		−4	mA
		V _{CC} = 5 V ± 0.5 V		−8	
I _{OL}	Low-level output current	V _{CC} = 2 V		50	μA
		V _{CC} = 3.3 V ± 0.3 V		4	mA
		V _{CC} = 5 V ± 0.5 V		8	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 3.3 V ± 0.3 V		100	ns/V
		V _{CC} = 5 V ± 0.5 V		20	

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

	MIN	NOM	MAX	UNIT
T _A Operating free-air temperature	–40		125	°C

- (1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74AHC595					UNIT
		BQB (WQFN)	D (SOIC)	DB (SSOP)	N (PDIP)	PW (TSSOP)	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	91.8	93.8	97.8	47.8	135.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	87.7	54.7	48.1	35.1	70.3	°C/W
R _{θJB}	Junction-to-board thermal resistance	61.6	50.9	48.5	27.8	81.3	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	11.9	20.8	10.0	20.1	22.5	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	61.4	50.7	47.9	27.7	80.8	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	39.4	—	—	—	—	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

PARAMETER	TEST CONDITIONS		V _{CC}	MIN	TYP	MAX	UNIT
V _{OH}	I _{OH} = –50 μA	T _A = 25°C	2 V	1.9	2		V
		T _A = –40°C to 85°C		1.9			
		T _A = –40°C to 125°C Recommended		1.9			
	I _{OH} = –50 μA	T _A = 25°C	3 V	2.9	3		
		T _A = –40°C to 85°C		2.9			
		T _A = –40°C to 125°C Recommended		2.9			
	I _{OH} = –50 μA	T _A = 25°C	4.5 V	4.4	4.5		
		T _A = –40°C to 85°C		4.4			
		T _A = –40°C to 125°C Recommended		4.4			
	I _{OH} = –4 mA	T _A = 25°C	3 V	2.58			
		T _A = –40°C to 85°C		2.48			
		T _A = –40°C to 125°C Recommended		2.48			
	I _{OH} = –8 mA	T _A = 25°C	4.5 V	3.94			
		T _A = –40°C to 85°C		3.8			
		T _A = –40°C to 125°C Recommended		3.8			

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

PARAMETER	TEST CONDITIONS		V _{CC}	MIN	TYP	MAX	UNIT
V _{OL}	I _{OL} = 50 μA	T _A = 25°C	2 V			0.1	V
		T _A = −40°C to 85°C				0.1	
		T _A = −40°C to 125°C Recommended				0.1	
	I _{OL} = 50 μA	T _A = 25°C	3 V			0.1	
		T _A = −40°C to 85°C				0.1	
		T _A = −40°C to 125°C Recommended				0.1	
	I _{OL} = 50 μA	T _A = 25°C	4.5 V			0.1	
		T _A = −40°C to 85°C				0.1	
		T _A = −40°C to 125°C Recommended				0.1	
	I _{OL} = 4 mA	T _A = 25°C	3 V			0.36	
		T _A = −40°C to 85°C				0.44	
		T _A = −40°C to 125°C Recommended				0.44	
	I _{OL} = 8 mA	T _A = 25°C	4.5 V			0.36	
		T _A = −40°C to 85°C				0.44	
		T _A = −40°C to 125°C Recommended				0.44	
I _I	V _I = 5.5 V or GND	T _A = 25°C	0 V to 5.5 V			±0.1	μA
		T _A = −40°C to 85°C				±1	
		T _A = −40°C to 125°C Recommended				±1	
I _{OZ}	V _I = V _{CC} or GND, V _O = V _{CC} or GND, OE = V _{IH} or V _{IL} ,	Q _A − Q _H	5.5 V			±0.25	μA
						±2.5	
						±2.5	
I _{CC}	V _I = V _{CC} or GND, I _O = 0	I _O = 0	5.5 V			4	μA
						40	
						40	
C _i	V _I = V _{CC} or GND	T _A = 25°C		5 V	3	10	pF
		T _A = −40°C TO 85°C				10	
C _O	V _O = V _{CC} or GND,	T _A = 25°C		5 V	5.5		pF

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested at V_{CC} = 0 V.

5.6 Timing Requirements: V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted)

				MIN	MAX	UNIT
t _w	Pulse duration	SRCLK high or low	T _A = 25°C	5		ns
			T _A = –40°C to 85°C	5		
			T _A = –40°C to 125°C Recommended	6		
	Pulse duration	RCLK high or low	T _A = 25°C	5		
			T _A = –40°C to 85°C	5		
			T _A = –40°C to 125°C Recommended	6		
	Pulse duration	SRCLR low	T _A = 25°C	5		
			T _A = –40°C to 85°C	5		
			T _A = –40°C to 125°C Recommended	6.5		

over recommended operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
t_{su}	Set-up time	SER before SRCLK↑	$T_A = 25^\circ\text{C}$	3.5	ns
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	3.5	
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	4.5	
	SRCLK↑ before RCLK↑ ⁽¹⁾		$T_A = 25^\circ\text{C}$	8	
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	8.5	
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	9.5	
	SRCLR low before RCLK↑		$T_A = 25^\circ\text{C}$	8	
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	9	
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	10	
	SRCLR high (inactive) before SRCLK↑		$T_A = 25^\circ\text{C}$	3	
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	3	
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	4	
t_h	Hold time	SER after SRCLK↑	$T_A = 25^\circ\text{C}$	1.5	ns
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1.5	
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	2.5	

(1) This set-up time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

5.7 Timing Requirements: $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

			MIN	NOM	MAX	UNIT
t_W	Pulse duration	SRCLK high or low	$T_A = 25^\circ\text{C}$	5		ns
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	6		
	RCLK high or low		$T_A = 25^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	6		
	SRCLR low		$T_A = 25^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	6.2		
t_{su}	Set-up time	SER before SRCLK↑	$T_A = 25^\circ\text{C}$	3		ns
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	3		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	4		
		SRCLK↑ before RCLK↑ ⁽¹⁾	$T_A = 25^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	6		
		SRCLR low before RCLK↑	$T_A = 25^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	5		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	6		
		SRCLR high (inactive) before SRCLK↑	$T_A = 25^\circ\text{C}$	2.5		
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	2.5		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	3.5		
t_h	Hold time	SER after SRCLK↑	$T_A = 25^\circ\text{C}$	2		ns
			$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	2		
			$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	3		

(1) This set-up time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

5.8 Switching Characteristics: $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f _{max}			C _L = 15 pF	T _A = 25°C	80 ⁽¹⁾	120 ⁽¹⁾	MHz	
				T _A = −40°C to 85°C	70			
				T _A = −40°C to 125°C Recommended	60			
			C _L = 50 pF	T _A = 25°C	55	105		
				T _A = −40°C to 85°C	50			
				T _A = −40°C to 125°C Recommended	40			
t _{PLH}	RCLK	Q _A − Q _H	C _L = 15 pF	T _A = 25°C	6 ⁽¹⁾	11.9 ⁽¹⁾	ns	
				T _A = −40°C to 85°C	1	13.5		
				T _A = −40°C to 125°C Recommended	1	14.9		
t _{PHL}	RCLK	Q _A − Q _H	C _L = 15 pF	T _A = 25°C	6 ⁽¹⁾	11.9 ⁽¹⁾	ns	
				T _A = −40°C to 85°C	1	13.5		
				T _A = −40°C to 125°C Recommended	1	14.9		
t _{PLH}	SRCLK	Q _{H'}	C _L = 15 pF	T _A = 25°C	6.6 ⁽¹⁾	13 ⁽¹⁾	ns	
				T _A = −40°C to 85°C	1	15		
				T _A = −40°C to 125°C Recommended	1	16.4		
t _{PHL}	SRCLK	Q _{H'}	C _L = 15 pF	T _A = 25°C	6.6 ⁽¹⁾	13 ⁽¹⁾	ns	
				T _A = −40°C to 85°C	1	15		
				T _A = −40°C to 125°C Recommended	1	16.4		
t _{PHL}	SRCLR	Q _{H'}	C _L = 15 pF	T _A = 25°C	6.2 ⁽¹⁾	12.8 ⁽¹⁾	ns	
				T _A = −40°C to 85°C	1	13.7		
				T _A = −40°C to 125°C Recommended	1	15		
t _{PZH}	OE	Q _A − Q _H	C _L = 15 pF	T _A = 25°C	6 ⁽¹⁾	11.5 ⁽¹⁾	ns	
				T _A = −40°C to 85°C	1	13.5		
				T _A = −40°C to 125°C Recommended	1	14.9		
t _{PZL}	OE	Q _A − Q _H	C _L = 15 pF	T _A = 25°C	7.8 ⁽¹⁾	11.5 ⁽¹⁾	ns	
				T _A = −40°C to 85°C	1	13.5		
				T _A = −40°C to 125°C Recommended	1	14.9		
t _{PLH}	RCLK	Q _A − Q _H	C _L = 50 pF	T _A = 25°C	7.9	15.4	ns	
				T _A = −40°C to 85°C	1	17		
				T _A = −40°C to 125°C Recommended	1	18.6		
t _{PHL}	RCLK	Q _A − Q _H	C _L = 50 pF	T _A = 25°C	7.9	15.4	ns	
				T _A = −40°C to 85°C	1	17		
				T _A = −40°C to 125°C Recommended	1	18.6		
t _{PLH}	SRCLK	Q _{H'}	C _L = 50 pF	T _A = 25°C	9.2	16.5	ns	
				T _A = −40°C to 85°C	1	18.5		
				T _A = −40°C to 125°C Recommended	1	20		
t _{PHL}	SRCLK	Q _{H'}	C _L = 50 pF	T _A = 25°C	9.2	16.5	ns	
				T _A = −40°C to 85°C	1	18.5		
				T _A = −40°C to 125°C Recommended	1	20		
t _{PHL}	SRCLR	Q _{H'}	C _L = 50 pF	T _A = 25°C	9	16.3	ns	
				T _A = −40°C to 85°C	1	17.2		
				T _A = −40°C to 125°C Recommended	1	18.7		
t _{PZH}	OE	Q _A − Q _H	C _L = 50 pF	T _A = 25°C	7.8	15	ns	
				T _A = −40°C to 85°C	1	17		
				T _A = −40°C to 125°C Recommended	1	18.6		

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PZL}	$\overline{OE}$	$Q_A - Q_H$	$C_L = 50 \text{ pF}$	$T_A = 25^\circ\text{C}$		9.6	15	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		17	
				$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	1		18.6	
t_{PHZ}	$\overline{OE}$	$Q_A - Q_H$	$C_L = 50 \text{ pF}$	$T_A = 25^\circ\text{C}$		8.1	15.7	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		16.2	
				$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	1		17.4	
t_{PLZ}	$\overline{OE}$	$Q_A - Q_H$	$C_L = 50 \text{ pF}$	$T_A = 25^\circ\text{C}$		9.3	15.7	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		16.2	
				$T_A = -40^\circ\text{C to } 125^\circ\text{C Recommended}$	1		17.4	

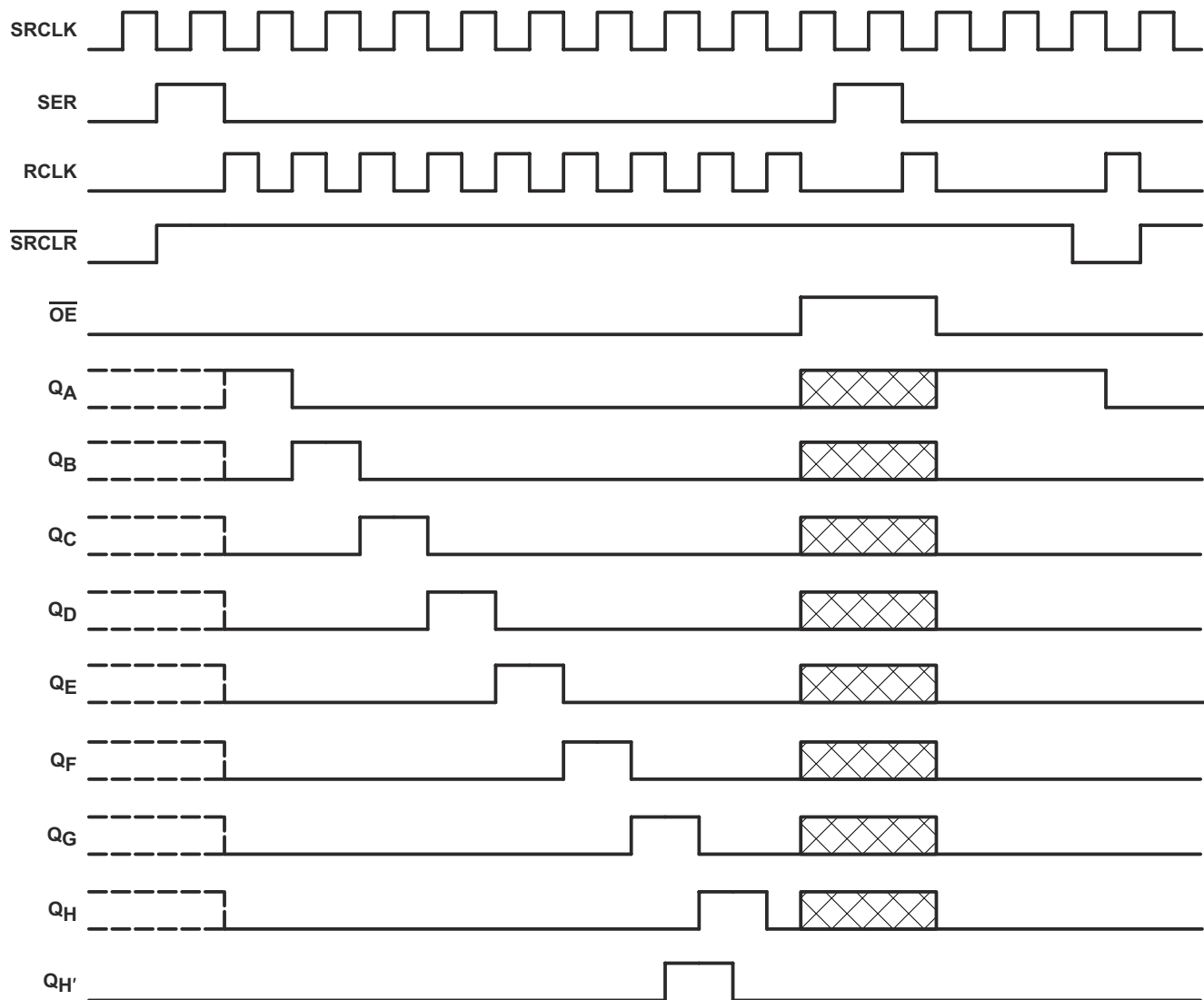
(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.

5.9 Switching Characteristics: $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over operating free-air temperature range (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$f_{\max}$			$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$	135 ⁽¹⁾	170 ⁽¹⁾		MHz
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	115			
			$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$	95	140		
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	85			
t_{PLH}	RCLK	$Q_A - Q_H$	$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$		4.3 ⁽¹⁾	7.4 ⁽¹⁾	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		8.5	
t_{PHL}	RCLK	$Q_A - Q_H$	$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$		4.3 ⁽¹⁾	7.4 ⁽¹⁾	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		8.5	
t_{PLH}	SRCLK	Q_H	$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$		4.5 ⁽¹⁾	8.2 ⁽¹⁾	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		9.4	
t_{PHL}	SRCLK	Q_H	$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$		4.5 ⁽¹⁾	8.2 ⁽¹⁾	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		9.4	
t_{PHL}	$\overline{\text{SRCLR}}$	Q_H	$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$		4.5 ⁽¹⁾	8 ⁽¹⁾	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		9.1	
t_{PZH}	$\overline{\text{OE}}$	$Q_A - Q_H$	$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$		4.3 ⁽¹⁾	8.6 ⁽¹⁾	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		10	
t_{PZL}	$\overline{\text{OE}}$	$Q_A - Q_H$	$C_L = 15\text{ pF}$	$T_A = 25^\circ\text{C}$		5.4 ⁽¹⁾	8.6 ⁽¹⁾	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		10	
t_{PLH}	RCLK	$Q_A - Q_H$	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		5.6	9.4	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		10.5	
t_{PHL}	RCLK	$Q_A - Q_H$	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		5.6	9.4	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		10.5	
t_{PLH}	SRCLK	Q_H	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		6.4	10.2	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		11.4	
t_{PHL}	SRCLK	Q_H	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		6.4	10.2	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		11.4	
t_{PHL}	$\overline{\text{SRCLR}}$	Q_H	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		6.4	10	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		11.1	
t_{PZH}	$\overline{\text{OE}}$	$Q_A - Q_H$	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		5.7	10.6	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		12	
t_{PZL}	$\overline{\text{OE}}$	$Q_A - Q_H$	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		6.8	10.6	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		12	
t_{PHZ}	$\overline{\text{OE}}$	$Q_A - Q_H$	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		3.5	10.3	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		11	
t_{PLZ}	$\overline{\text{OE}}$	$Q_A - Q_H$	$C_L = 50\text{ pF}$	$T_A = 25^\circ\text{C}$		3.4	10.3	ns
				$T_A = -40^\circ\text{C to } 85^\circ\text{C}$	1		11	

(1) On products compliant to MIL-PRF-38535, this parameter is not production tested.



NOTE:  implies that the output is in 3-State mode.

图 5-1. Timing Diagram

5.10 Operating Characteristics

$V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	No load, $f = 1\text{ MHz}$	25.2	pF

5.11 Typical Characteristics

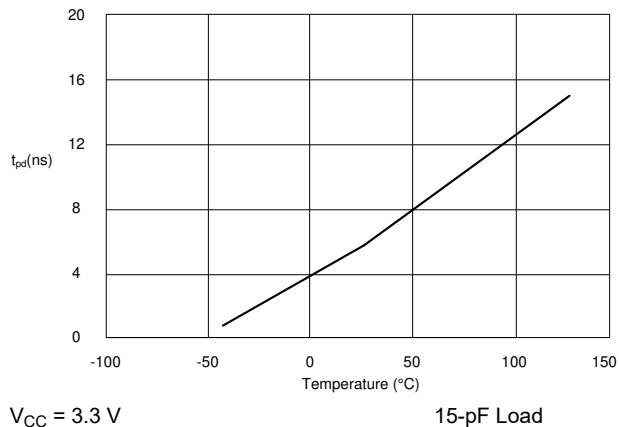
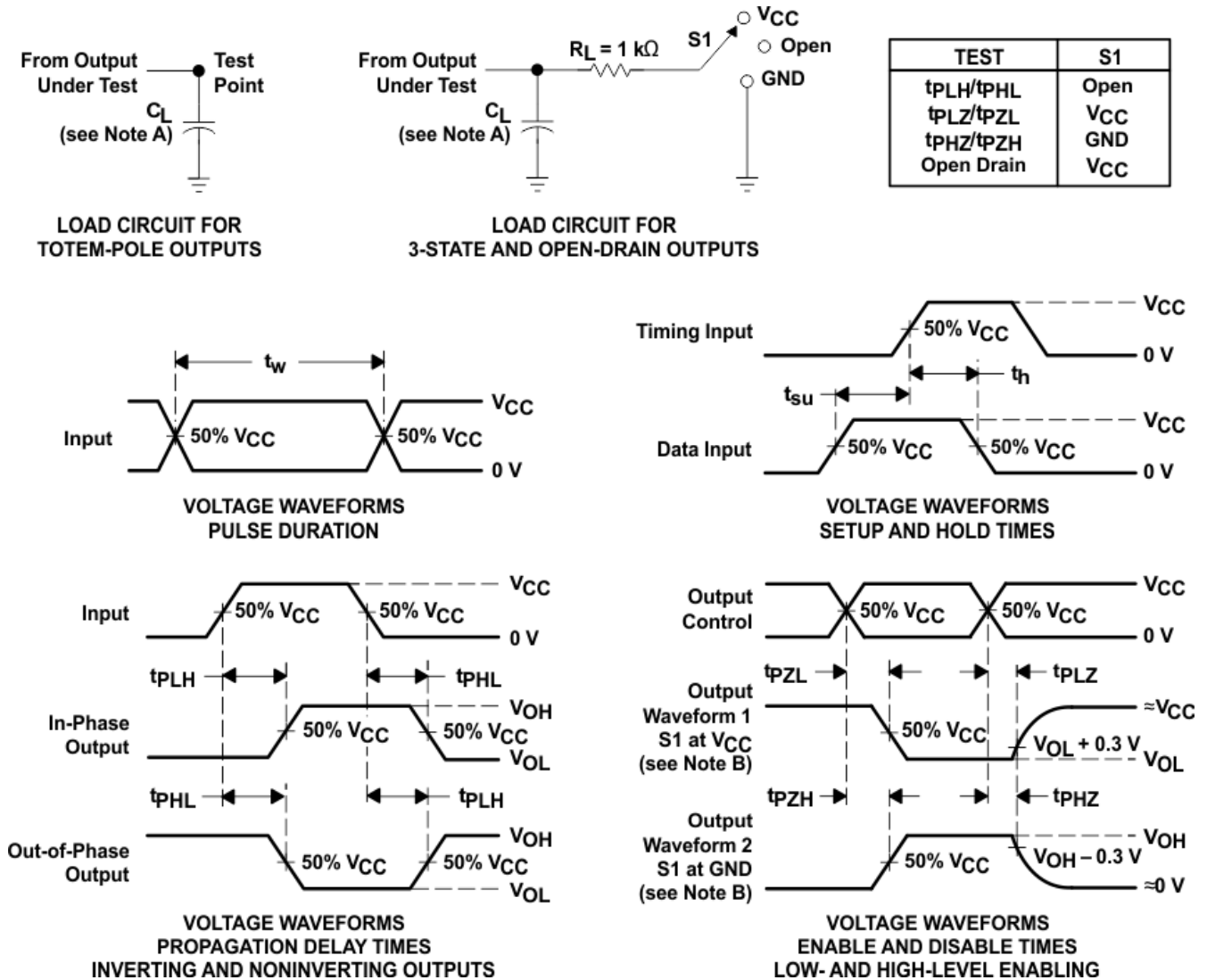


图 5-2. SN74AHC595 RCLK to Q TPD vs Temperature

6 Parameter Measurement Information



- A. C_L includes probe and jig capacitance.
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 3\text{ ns}$, $t_f \leq 3\text{ ns}$.
- D. The outputs are measured one at a time with one input transition per measurement.
- E. All parameters and waveforms are not applicable to all devices.

图 6-1. Load Circuit and Voltage Waveforms

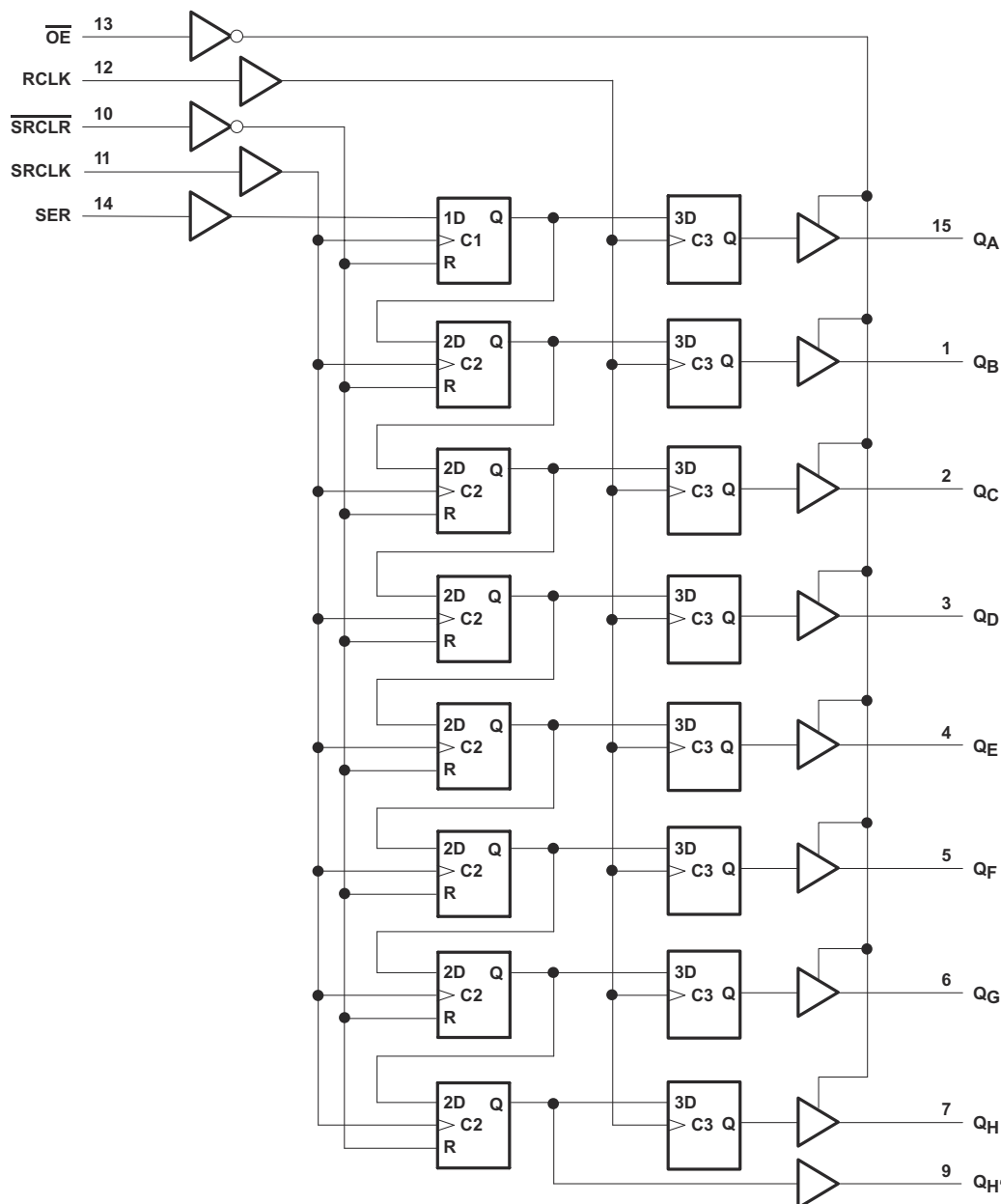
7 Detailed Description

7.1 Overview

The SN74AHC595 device is part of the AHC family of logic devices intended for CMOS applications. The SN74HC595 device is an 8-bit shift register that feeds an 8-bit D-type storage register.

Both the shift-register clock (SRCLK) and storage-register clock (RCLK) are positive-edge triggered. If both clocks are connected together, the shift register is always one clock pulse ahead of the storage register.

7.2 Functional Block Diagram



7.3 Feature Description

The SN74AHC595 device is an 8-bit serial-in, parallel-out shift registers that have a wide operating voltage range from 2 V to 5.5 V and a low current consumption of 40- μ A (max) I_{CC} .

7.4 Device Functional Modes

表 7-1. Function Table

INPUTS					FUNCTION
SER	SRCLK	SRCLR	RCLK	OE	
X	X	X	X	H	Outputs Q _A –Q _H are disabled.
X	X	X	X	L	Outputs Q _A –Q _H are enabled.
X	X	L	X	X	Shift register is cleared.
L	↑	H	X	X	First stage of the shift register goes low. Other stages store the data of previous stage, respectively.
H	↑	H	X	X	First stage of the shift register goes high. Other stages store the data of previous stage, respectively.
X	X	X	↑	X	Shift-register data is stored into the storage register.

8 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

8.1 Application Information

The SN74AHC595 device is a low-drive CMOS device that can be used for a multitude of bus-interface type applications where output ringing is a concern. The low drive and slow edge rates minimize overshoot and undershoot on the outputs. 图 8-1 shows an application where eight LEDs are used to visualize the data bits contained within the shift register.

8.2 Typical Application

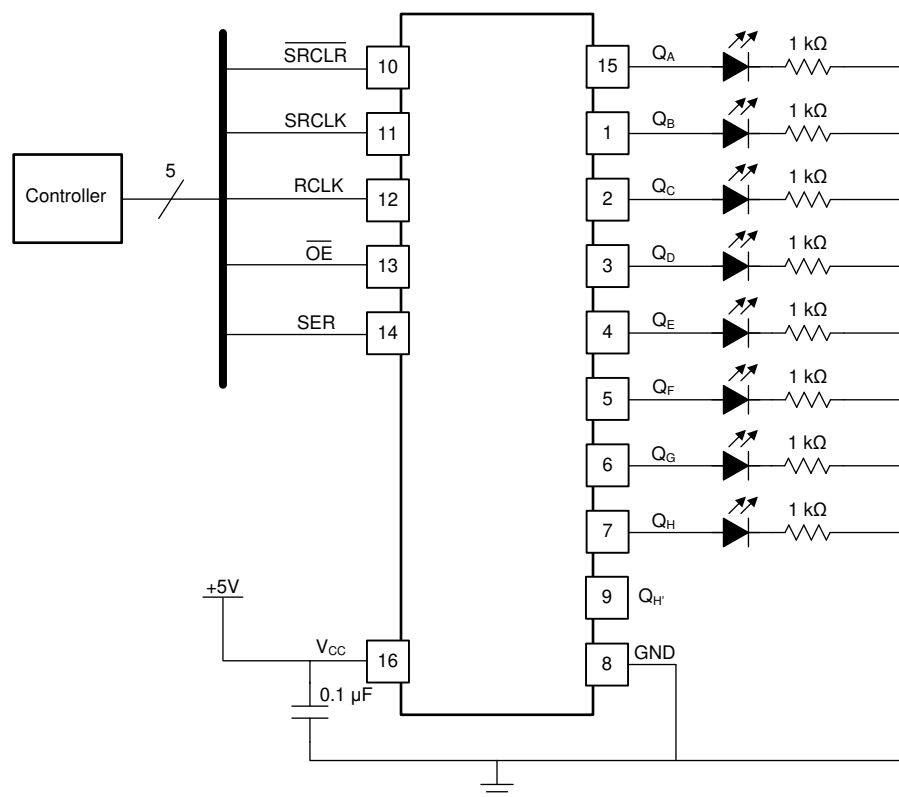


图 8-1. Shift Register Display of 8 bits

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care must be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions must be considered to prevent ringing.

8.2.2 Detailed Design Procedure

- Recommended input conditions:
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the [Recommended Operating Conditions](#) table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the [Recommended Operating Conditions](#) table.
 - Inputs are overvoltage tolerant allowing them to go as high as 6.0 V at any valid V_{CC}
- Recommend output conditions:
 - Load currents must not exceed 25 mA per output and 75 mA total for the part

- Outputs must not be pulled above V_{CC}

8.2.3 Application Curve

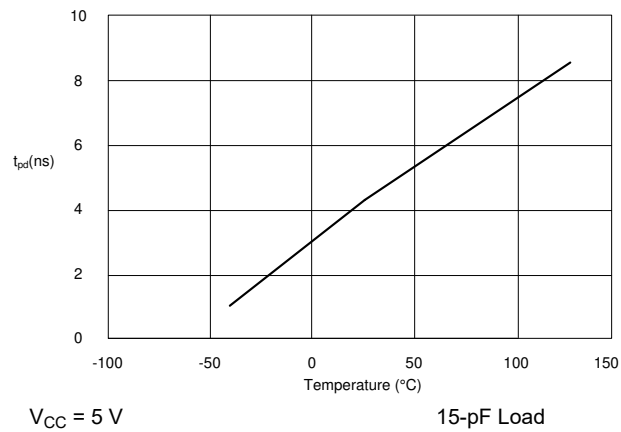


图 8-2. SN74AHC595 RCLK to Q TPD vs Temperature

8.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply-voltage rating located in the [Recommended Operating Conditions](#) table.

Each V_{CC} pin must have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1- μ F capacitor is recommended; if there are multiple V_{CC} pins, then a 0.01- μ F or a 0.022- μ F capacitor is recommended for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. A 0.1- μ F and a 1- μ F capacitor are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-bit logic devices, inputs must never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins must **not** be left unconnected because the undefined voltages at the outside connections results in undefined operational states. [Figure 8-3](#) specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, these unused inputs will be tied to GND or V_{CC} , whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output-enable pin, it will disable the output section of the part when asserted. This will not disable the input section of the I/Os, so they cannot float when disabled.

8.4.2 Layout Example

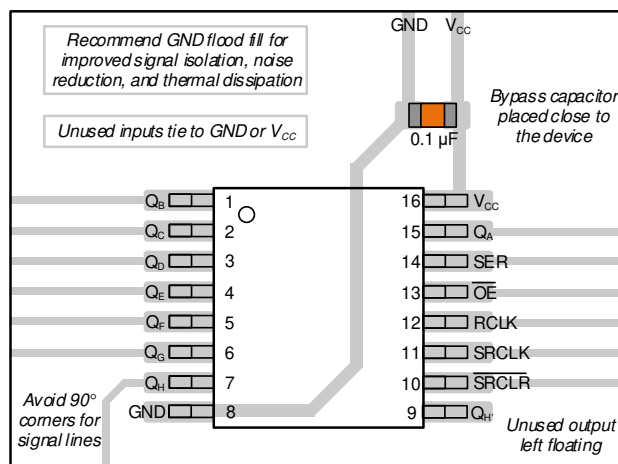


图 8-3. Example Layout for the SN74AHC595

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

Implications of Slow or Floating CMOS Inputs, [SCBA004](#)

9.2 接收文档更新通知

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9.3 支持资源

[TI E2E™ 中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

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9.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

10 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision M (April 2024) to Revision N (July 2024)	Page
• Updated R θ JA value: D = 73 to 93.8, all values in °C/W	5

Changes from Revision L (March 2024) to Revision M (April 2024)	Page
• Updated thermal values for PW package from R θ JA = 106.1 to 135.9, R θ JC(top) = 40.8 to 70.3, R θ JB = 51.1 to 81.3, Ψ JT = 3.8 to 22.5, Ψ JB = 50.6 to 80.8, all values in °C/W.....	5
• Added <i>Typical Characteristics</i>	12
• Updated <i>Layout Example</i>	18

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74AHC595BQBR	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC595	Samples
SN74AHC595D	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 125	AHC595	
SN74AHC595DBR	ACTIVE	SSOP	DB	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HA595	Samples
SN74AHC595DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHC595	Samples
SN74AHC595N	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 125	SN74AHC595N	Samples
SN74AHC595PW	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 125	HA595	
SN74AHC595PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HA595	Samples
SN74AHC595PWRG4	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HA595	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN74AHC595 :

- Automotive : [SN74AHC595-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

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